



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

PATENT

AF

1765

Applicant: E. Morita

Serial No.: 09/726,860

Filed: November 30, 2000

For: METHOD OF MANUFACTURING
CRYSTAL OF III-V COMPOUND OF THE
NITRIDE SYSTEM, CRYSTAL
SUBSTRATE OF III-V COMPOUND OF
THE NITRIDE SYSTEM, CRYSTAL FILM
OF III-V COMPOUND OF THE NITRIDE
SYSTEM, AND METHOD OF
MANUFACTURING DEVICE

Case No.: 9792909-4715

Examiner: M. Anderson

Group Art Unit: 1765

Certificate of Mailing (37 CFR 1.8(a))

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Date of Deposit: March 31, 2003

David R. Metzger
Date

Date

TRANSMITTAL LETTER

Assistant Commissioner for Patents
Washington, D.C. 20231

Dear Sir:

Enclosed herewith is a Response D to Final Office Action.

Also enclosed are:

Return Receipt Postcard

The Commissioner is hereby authorized to charge any additional fees
required, as well as any patent application processing fees associated with this
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No. 19-3140. A duplicate copy of this sheet is enclosed.

Respectfully submitted,

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In the United States Patent and Trademark Office

Inventor: E. Morita

Serial No.: 09/726,860

Title: Method of Manufacturing Crystal of III-V...

Atty. Docket No. 9792909-4715

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Response D to Final Office Action dated 04 Feb. 2003

In response to the Final Office Action dated 04 Feb. 2003, the applicant responds as follows.

A. In the Claims

1. (currently amended) A method of manufacturing a crystal of a III-V compound of the nitride system, the method including:

(a) a first growth step to form a first crystal layer, the first crystal layer further having a surface, by growing a crystal of a III-V compound of the nitride system on a surface of a basal body;

(b) a first mask forming step to form a first mask pattern on the surface of the first crystal layer;

(c) a first etching step to etch the first crystal layer through the first mask pattern;

(d) a second growth step to form a second crystal layer, the second crystal layer further having a surface, by growing a crystal of a III-V compound of the nitride system from the first crystal layer;

(e) a second mask forming step to form a second mask pattern on the surface of the second crystal layer and ensuring that the second mask overlies a window in the first mask;